



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD.

TO-252-2L Plastic-Encapsulate MOSFETS

CJU30N10 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	24mΩ@10V	30A

DESCRIPTION

This advanced high voltage MOSFET is designed to stand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode fast recovery time. Designed for high voltage, high speed switching applications such as power supplies,

converters, power motor controls and bridge circuits.

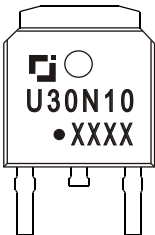
FEATURES

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Special process technology for high ESD capability
- Excellent package for good heat dissipation

APPLICATIONS

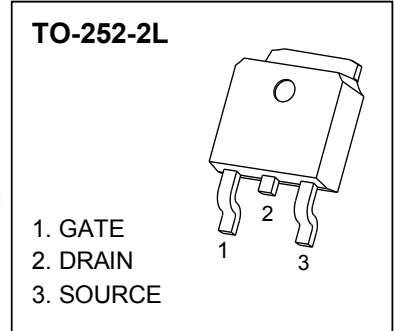
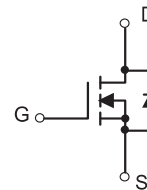
- Hard switched and high frequency circuits
- Uninterruptible power supply
- Power switching application

MARKING



U30N10 = Device code.
Solid dot = Green molding compound device if none, the normal device.
XXXX = Code.

EQUIVALENT CIRCUIT



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D ①	30	A
Pulsed Drain Current	I_{DM} ②	120	A
Single Pulsed Avalanche Energy	E_{AS} ③	156	mJ
Maximum Power Dissipation	P_D ①	85	W
Thermal Resistance from Junction to Ambient	R_{JA} ⑥	100	°C/W
Thermal Resistance from Junction to Case	$R_{\theta JC}$ ①	1.47	°C/W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

MOSFET ELECTRICAL CHARACTERISTICS

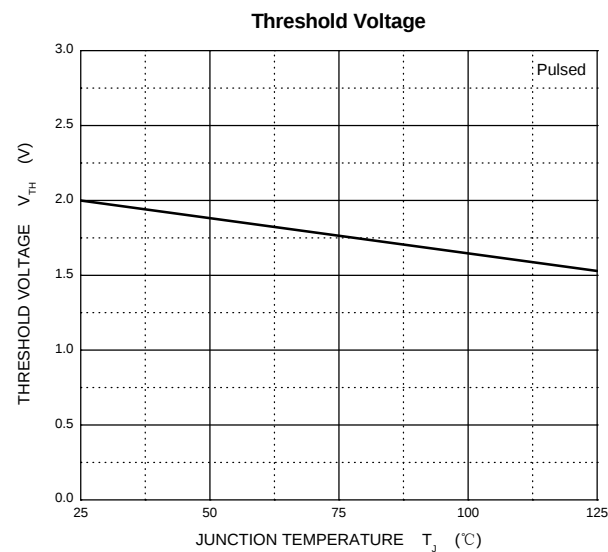
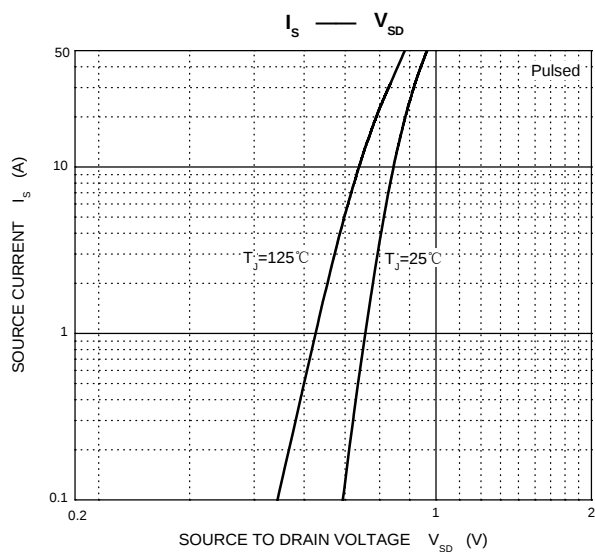
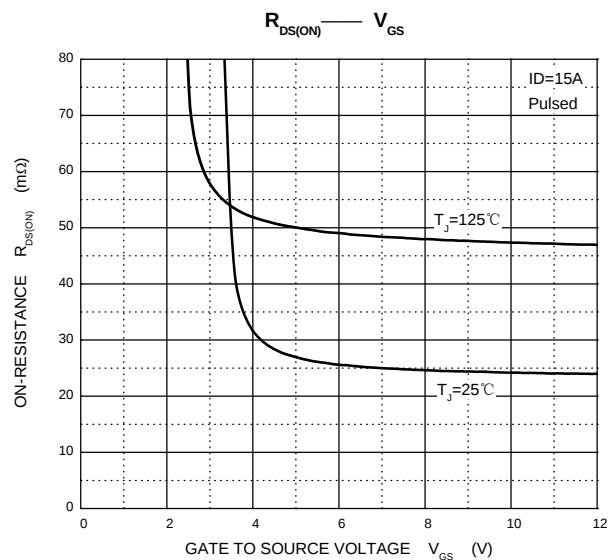
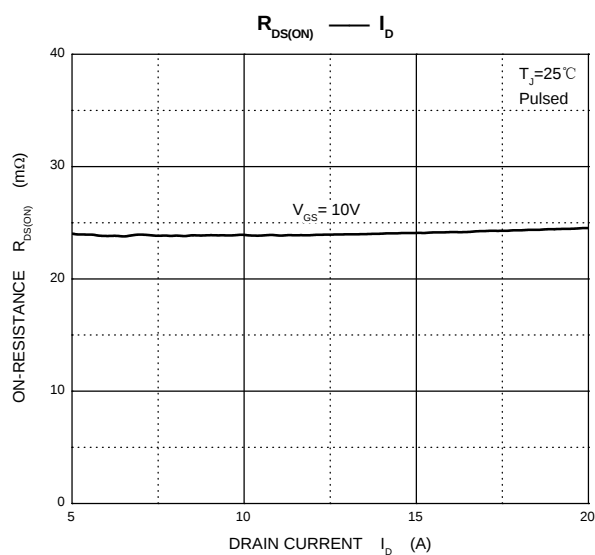
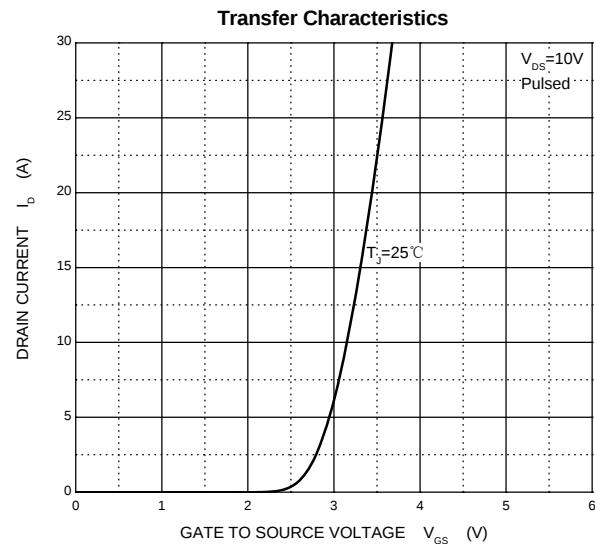
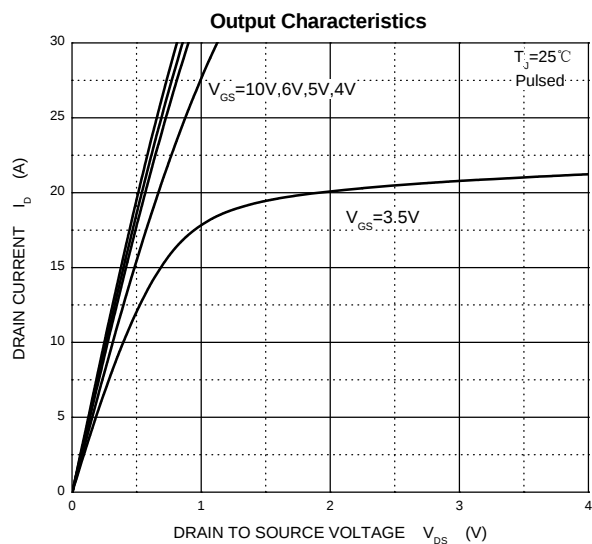
$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Off characteristics							
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA		100			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =80V,	T _J =25 ℃			1	μA
		V _{GS} =0V	T _J =125 ℃			100	
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V				±100	nA
On characteristics ^④							
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA		1.3	2.0	2.5	V
Static drain-source on-sate resistance	R _{DS(on)}	V _{GS} =10V, I _D =15A			24	31	mΩ
Forward transconductance	g _{FS}	V _{DS} =5V, I _D =10A			15		S
Dynamic characteristics ^{④ ⑤}							
Input capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V, f =1MHz			2465	4930	pF
Output capacitance	C _{Oss}				118	236	
Reverse transfer capacitance	C _{rss}				108	216	
Gate resistance	R _g	f =1MHz			2.3		Ω
Switching characteristics ^{④ ⑤}							
Total gate charge	Q _g	V _D S=50V,V _G S=10V, I _D =10A			62	124	nC
Gate-source charge	Q _{gs}				6.2	12	
Gate-drain charge	Q _{gd}				15	30	
Turn-on delay time	t _{d(on)}	V _D S=30V, V _G S=10V,ID=2A, R _G =3Ω , R _L =5Ω			7		ns
Turn-on rise time	t _r				7		
Turn-off delay time	t _{d(off)}				29		
Turn-off fall time	t _f				7		
Drain-Source Diode Characteristics							
Drain-source diode forward voltage	V _{SD} ^④	V _{GS} =0V, I _S =40A				1.2	V
Continuous drain-source diode forward current	I _S ^①					30	A
Pulsed drain-source diode forward current	I _{SM} ^②					120	A

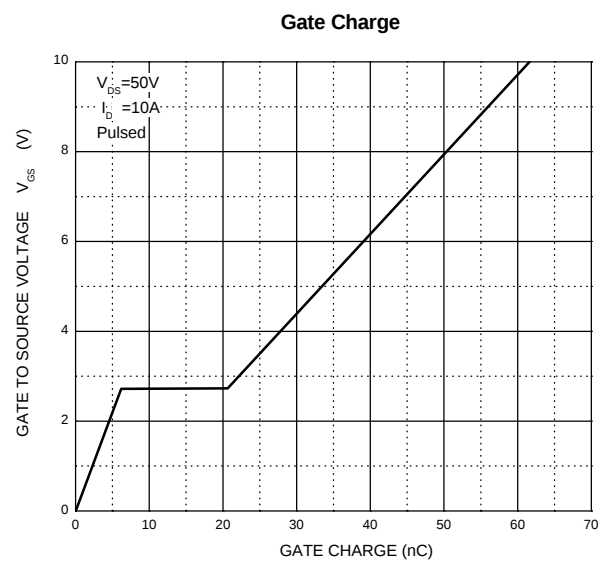
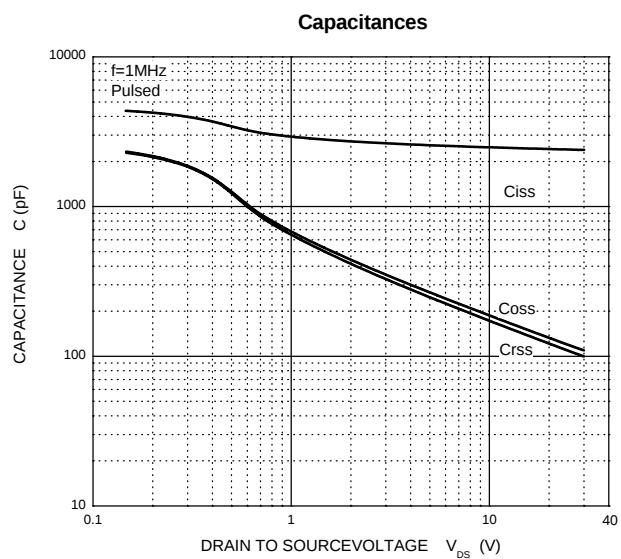
Notes:

1. $T_C = 25^{\circ}\text{C}$ Limited only by maximum temperature allowed.
2. $P_W \leq 10\mu s$, Duty cycle $\leq 1\%$.
3. EAS condition: $V_{DD} = 50V, V_{GS} = 10V, L = 0.5\text{mH}, R_g = 25\Omega$ Starting $T_J = 25^{\circ}\text{C}$.
4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. Guaranteed by design, not subject to production.
6. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a = 25^{\circ}\text{C}$.

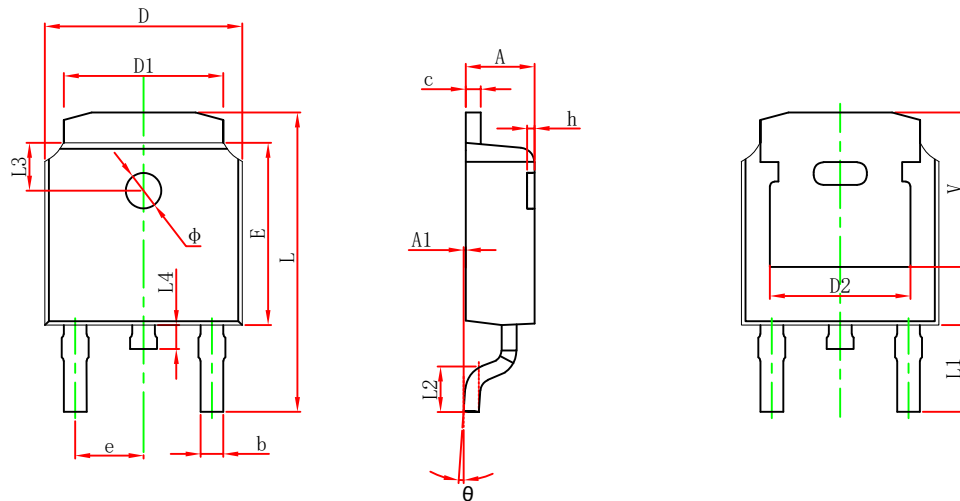
Typical Characteristics



Typical Characteristics

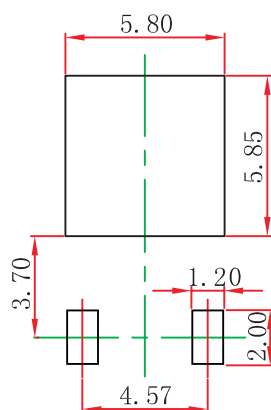


TO-252-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggested Pad Layout



Note:

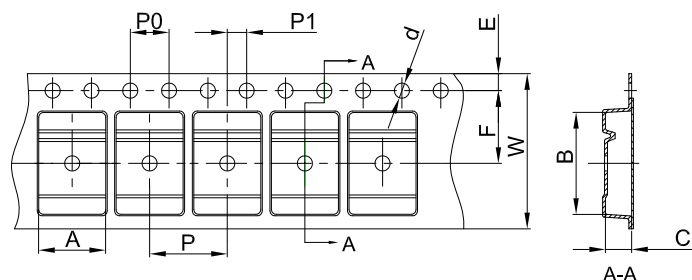
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

TO-252-2L Tape and Reel

TO-252 Embossed Carrier Tape

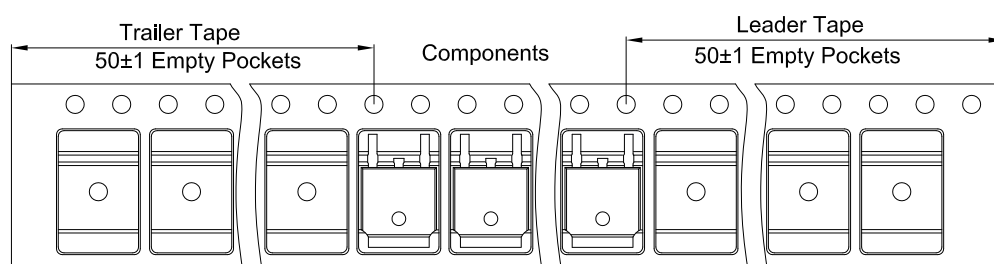


Packaging Description:

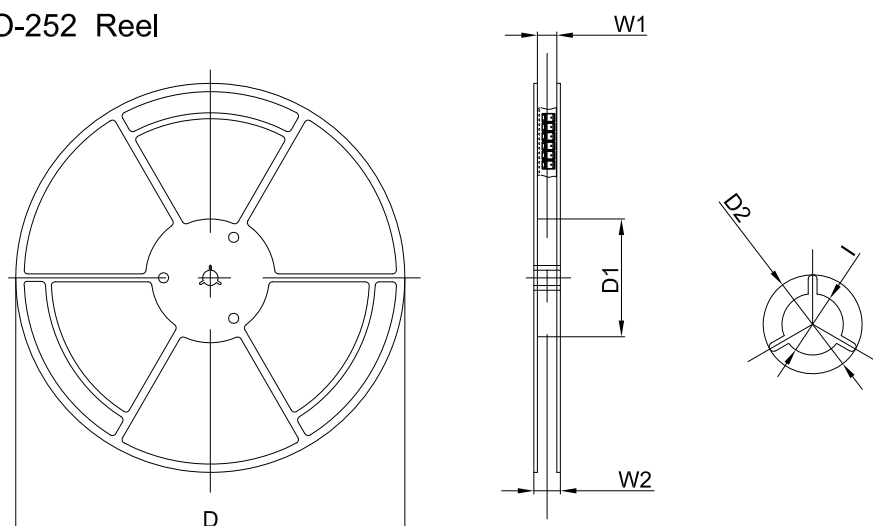
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer



TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	